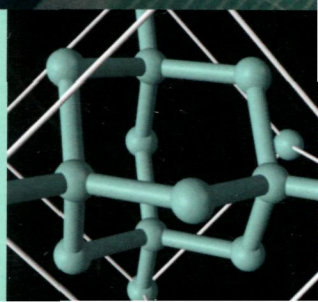


Advanced Silicon Materials for Photovoltaic Applications

Editor SERGIO PIZZINI

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Contents

<i>Preface</i>	xi
<i>List of Contributors</i>	xv
1. Silicon Science and Technology as the Background of the Current and Future Knowledge Society	1
<i>Sergio Pizzini</i>	
1.1 Introduction	1
1.2 Silicon Birth from a Thermonuclear Nucleosynthetic Process	2
1.3 Silicon Key Properties	2
1.3.1 Chemical and Structural Properties	2
1.3.2 Point Defects	7
1.3.3 Radiation Damage and Radiation Hardness	7
1.4 Advanced Silicon Applications	9
1.4.1 Silicon Radiation Detectors	9
1.4.2 Photovoltaic Cells for Space Vehicles and Satellite Applications	11
1.4.3 Advanced Components Based on the Dislocation Luminescence in Silicon	12
1.4.4 Silicon Nanostructures	14
References	15
2. Processes	21
<i>Bruno Ceccaroli and Sergio Pizzini</i>	
2.1 Introduction	21
2.2 Gas-Phase Processes	23
2.2.1 Preparation and Synthesis of Volatile Silicon Compounds	23
2.2.2 Purification of Volatile Silicon Compounds	30
2.2.3 Decomposition of Volatile Precursors to Elemental Silicon	30
2.2.4 Most Common Reactors	33
2.2.5 Recovery of By-Products	38
2.3 Production of MG and UMG Silicon and Further Refining Up to Solar Grade by Chemical and Physical Processes	40
2.3.1 MG Silicon Production	42
2.3.2 Metallurgical Refining Processes	47
2.3.3 Metal–Metal Extraction Processes	52

2.3.4	Solid/Liquid Extraction Techniques	54
2.3.5	Final Purification by Directional Solidification	55
2.3.6	Solar-Grade Silicon Production from Pure Raw Materials or Via the Direct Route	58
2.4	Fluoride Processes	59
2.5	Silicon Production/Refining with High-Temperature Plasmochemical Processes	61
2.5.1	Silicon Production Via Plasma Processes	62
2.5.2	Silicon Refining Via Plasma Processes	63
2.6	Electrochemical Processes: Production of Silicon Without Carbon as Reductant	64
2.7	Conclusions	68
	Acknowledgements	69
	References	70
3.	Role of Impurities in Solar Silicon	79
	<i>Gianluca Coletti, Daniel Macdonald and Deren Yang</i>	
3.1	Introduction	79
3.2	Sources and Refinements of Impurities	79
3.3	Segregation of Impurities During Silicon Growth	86
3.3.1	Equilibrium Segregation Coefficients	86
3.3.2	Effective Segregation Coefficient	87
3.3.3	Distribution of Impurities in Silicon Crystal Due to Segregation	90
3.4	Role of Metallic Impurities	92
3.4.1	Solubility and Diffusivity	92
3.4.2	Impact on Charge-Carrier Recombination	94
3.4.3	Modeling the Impact of Metallic Impurities on the Solar-Cell Performance	96
3.5	Role of Dopants	101
3.5.1	Carrier Mobilities in Compensated Silicon	101
3.5.2	Recombination in Compensated Silicon	103
3.5.3	Dopant-Related Recombination Centers	105
3.5.4	Segregation Effects During Ingot Growth	106
3.5.5	Detecting Dopants in Compensated Silicon	107
3.6	Role of Light Elements	108
3.6.1	Oxygen	108
3.6.2	Carbon	109
3.6.3	Nitrogen	111
3.6.4	Germanium	113
3.7	Arriving at Solar-Grade Silicon Feedstock Definitions	114
	References	118
4.	Gettering Processes and the Role of Extended Defects	127
	<i>Michael Seibt and Vitaly Kveder</i>	
4.1	Introduction	127

4.2	Properties of Transition-Metal Impurities in Silicon	130
4.2.1	Solubility of Transition-Metal Impurities	131
4.2.2	Diffusion of Transition-Metal Impurities	136
4.3	Gettering Mechanisms and their Modeling	139
4.3.1	Segregation Gettering	140
4.3.2	Relaxation Gettering	142
4.3.3	Injection Gettering	142
4.3.4	Modeling of Gettering Kinetics	143
4.3.5	Aluminum Gettering	144
4.3.6	Phosphorus-Diffusion Gettering	146
4.3.7	Boron-Diffusion Gettering	149
4.4	Bulk Processes Affecting Gettering Efficiency and Kinetics	150
4.4.1	Metal-Silicide Precipitates	150
4.4.2	Dislocations	154
4.4.3	Grain Boundaries	167
4.4.4	Light-Element Impurities and Related Defects	169
4.5	Gettering Strategies and Defect Engineering	170
4.6	Conclusions	173
	Acknowledgements	173
	References	174
5.	Advanced Characterization Techniques	189
	<i>Anna Cavallini, Daniela Cavalcoli and Laura Polenta</i>	
5.1	Introduction	189
5.2	Surface Photovoltage Spectroscopy	190
5.2.1	The Basic Principles	191
5.2.2	SPS Setup	193
5.2.3	Surface Photovoltage Spectroscopy of Hydrogenated Nanocrystalline Silicon (nc-Si:H)	194
5.3	Photocurrent Spectroscopy	196
5.3.1	Basic Principles	197
5.3.2	Spectral Photoconductivity Setup	199
5.3.3	Application of Spectral Photoconductivity to Silicon and Silicon Devices	201
5.4	Optical (Light) Beam Induced Current (OBIC or LBIC)	202
5.4.1	Basic Principles of Optical Beam Induced Current Method	202
5.4.2	Determination of the Electric Field and Depletion Region Extent in Particle Detectors by OBIC	204
5.5	Scanning Probe Microscopy for the Nanoscale Electrical Characterization of Semiconductors for PV Applications	207
5.6	Concluding Remarks	210
	References	210
6.	Advanced Analytical Techniques for Solar-Grade Feedstock	215
	<i>Richard S. Hockett</i>	
6.1	Introduction	215

6.2	Review of Analytical Techniques	216
6.3	GDMS Analysis of PV Si	222
6.4	SIMS Analysis of PV Si	223
6.5	Applications of SIMS and GDMS for PV Si Feedstock Studies	227
6.5.1	Impurity Segregation in Directional Solidified (DS) Silicon Blocks	227
6.5.2	Specification of [C], [O] and [N] in Solar-Grade Silicon Feedstock to be Used in DS Furnaces	229
6.5.3	SIMS Capability for Reduced-Cost Measurement of [C, O, B, P]	230
6.5.4	Problems in Conversion Between Resistivity and Dopant Concentration in Highly Compensated Silicon	231
	References	232
7.	Thin-Film Deposition Processes	235
	<i>J.K. Rath</i>	
7.1	Introduction	235
7.2	Deposition Techniques of Thin-Film Silicon	235
7.2.1	Standard Radio-Frequency Plasma-Enhanced CVD	236
7.2.2	Very High Frequency Plasma-Enhanced CVD	236
7.2.3	Microwave Plasma-Enhanced CVD	237
7.2.4	Expanded Thermal Plasma (ETP) Deposition	237
7.2.5	Low-Energy Plasma-Enhanced PECVD	238
7.2.6	Hot-Wire CVD	238
7.3	<i>In Situ</i> Diagnosis of Growth Conditions	239
7.3.1	Electrical: Current–Voltage ($I-V$) Probe	239
7.3.2	Optical Emission Spectroscopy (OES)	240
7.3.3	Infrared Spectroscopy	243
7.3.4	Ellipsometry	244
7.3.5	Ion Energy Probe	245
7.4	Challenges of Deposition at High Growth Rates and Low Substrate Temperatures	246
7.4.1	Growth-Process Models	246
7.4.2	Inhomogeneity of Growth	250
7.4.3	Growth at High Deposition Rates	251
7.4.4	Silane Dissociation Efficiency and Depletion Criteria for nc-Si Deposition	252
7.4.5	Low-Temperature (LT) Deposition	254
7.4.6	Structural Evolution at Low Temperature	257
7.4.7	Transient Plasma	260
7.5	Upscaling to Large-Area and Industrial Processing: Critical Analysis of Various Fabrication Processes	270
	Acknowledgements	273
	References	273

8. Modeling of Thin-Film Deposition Processes	287
<i>Carlo Cavallotti</i>	
8.1 Introduction	287
8.2 Modeling the Plasma Discharge	290
8.3 Modeling of the Gas Phase and Surface Kinetics	295
8.3.1 Gas-Phase Kinetic Scheme	297
8.3.2 Surface Kinetic Scheme	301
8.3.3 On the Consistent Solution of the Plasma Discharge and Kinetic Models: Theory and Examples	303
8.4 Modeling of the Thin-Film Morphological Evolution	303
8.5 Status of the Field and Perspectives	308
References	309
9. Thin-Film Silicon Solar Cells	311
<i>J.K. Rath</i>	
9.1 Introduction	311
9.2 Second-Generation Solar Cells: Advantages Compared to the First Generation	312
9.3 Drift-Type Thin-Film Silicon Solar Cells: Substrates and Configuration	314
9.4 Material Considerations for Thin-Film Silicon Solar Cells	316
9.4.1 Amorphous Silicon	316
9.4.2 Amorphous Silicon-Germanium	317
9.4.3 Nanocrystalline Silicon	317
9.4.4 Light Confinement	318
9.5 Present Status of Drift-Type Thin-Film Silicon Solar Cells	321
9.5.1 Recent R&D Results on Thin-Film Silicon Solar Cells	322
9.5.2 Industrial Scenario	322
9.6 Technological Issues	325
9.6.1 High Deposition Rate	325
9.6.2 Thin Cells	325
9.7 Third-Generation Thin-Film Silicon Cell	329
9.8 Solar Cells on Plastics	331
9.8.1 Transfer Method	331
9.8.2 Direct Deposition	332
9.9 Hybrid Cells	334
9.10 Industrial Scenario of Thin-Film Silicon-based Solar Cells	336
9.11 Challenges for Thin-Film Silicon Solar-Module Fabrication	338
Acknowledgements	341
References	341
10. Innovative Quantum Effects in Silicon for Photovoltaic Applications	355
<i>Zhizhong Yuan, Aleksei Anopchenko and Lorenzo Pavesi</i>	
10.1 Basic Principles of 3 rd -Generation Solar Cells	355
10.1.1 The Need for a New Generation of Solar Cells	355

10.1.2	Limitations in Early Generations	356
10.1.3	3 rd -Generation Options	357
10.2	The Advantages of Using Silicon Nanocrystals	359
10.2.1	Fabrication and Advantages of Si-NCs	359
10.2.2	Quantum Confinement Effect in Si-NCs	360
10.3	Applications of Si-NCs in the 3 rd -Generation Solar Cells	362
10.3.1	All-Silicon Tandem Solar Cells	362
10.3.2	Hot-Carrier Solar Cells	364
10.3.3	Intermediate-Band Solar Cells	366
10.3.4	Multiple-Carrier Generation	369
10.3.5	Downshifter Cell	372
10.4	Challenges and Solutions	375
10.4.1	Size Control	375
10.4.2	Carrier Transport	375
10.4.3	Absorption	378
10.4.4	Technological Constraints	381
10.5	Conclusions	381
	Acknowledgements	381
	References	381
	Index	393